

### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I <sub>D</sub>	250 170	mA
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	800	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

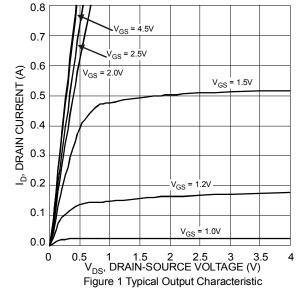
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady state	$P_D$	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	402	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

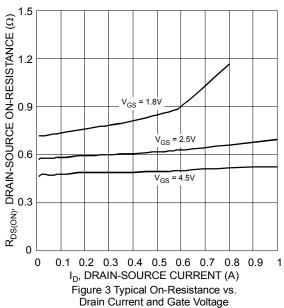
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

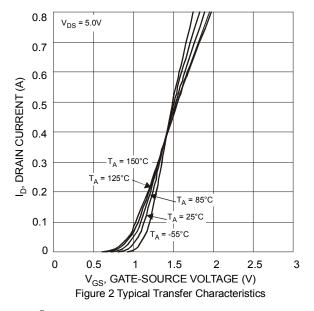
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	20	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current @Tc	= +25°C	I <sub>DSS</sub>	_	_	100	nA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		$V_{GS(th)}$	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
				0.60	0.99		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA	
			_	0.75	1.2	Ω	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA	
Static Drain-Source On-Resistance		R <sub>DS(ON)</sub>	_	0.90	1.8		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 20mA	
			_	1.2	2.4		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA	
			-	2.0	_		V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 1mA	
Forward Transfer Admittance		Y <sub>fs</sub>	180	_	_	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 400mA	
Diode Forward Voltage		$V_{SD}$	-	0.6	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 150mA	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		$C_{\text{iss}}$	_	28.2	55.2	pF	-V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Output Capacitance		Coss	_	4.0	8.0	pF		
Reverse Transfer Capacitance		C <sub>rss</sub>	_	2.8	5.6	pF		
Total Gate Charge		Qg	_	0.5	1.0	nC		
Gate-Source Charge		Q <sub>gs</sub>	_	0.07	0.14	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$	
Gate-Drain Charge		Q <sub>gd</sub>	-	0.07	0.14	nC		
Turn-On Delay Time		t <sub>D(on)</sub>		3.5	10	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_{L} = 47\Omega, R_{G} = 10\Omega,$ $I_{D} = 200 \text{mA}$	
Turn-On Rise Time		t <sub>r</sub>	-	2.1	10	ns		
Turn-Off Delay Time		t <sub>D(off)</sub>	-	22	35	ns		
Turn-Off Fall Time		t <sub>f</sub>	_	7.7	15	ns		

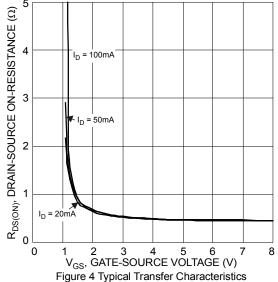
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
   Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.



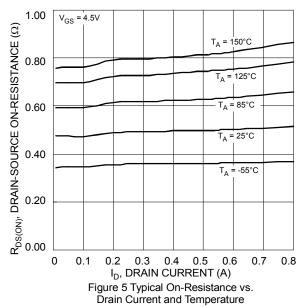


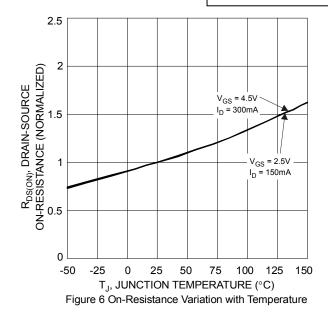


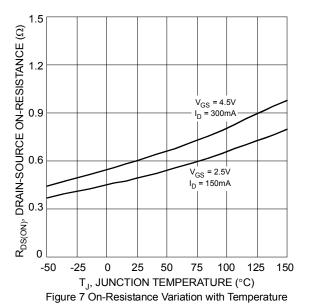












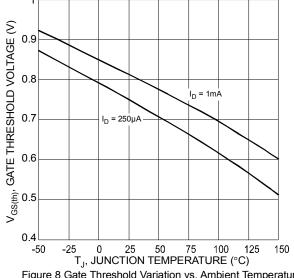
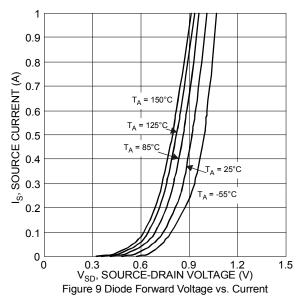
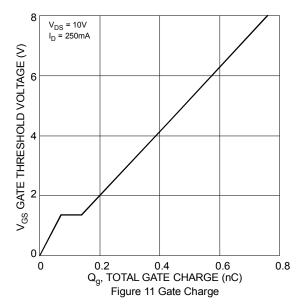
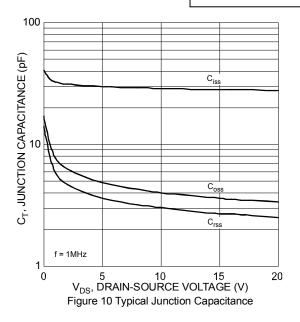


Figure 8 Gate Threshold Variation vs. Ambient Temperature





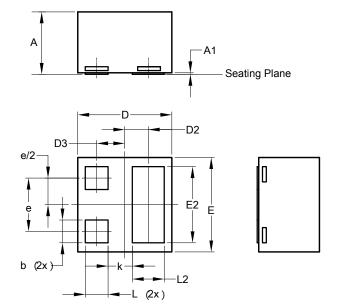






## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

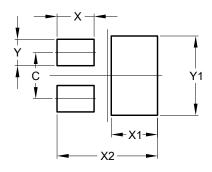


X2-DFN0606-3					
Dim	Min	Max	Тур		
Α	0.36	0.40	0.39		
A1	0	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57	0.67	0.62		
D2	0.155 BSC				
D3	0.185 BSC				
Е	0.57	0.67	0.62		
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
L	0.09	0.21	0.15		
L2	0.11	0.31	0.21		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### X2-DFN0606-3



Dimensions	Value (in mm)
С	0.350
Х	0.280
X1	0.350
X2	0.760
Υ	0.200
V1	0.600



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